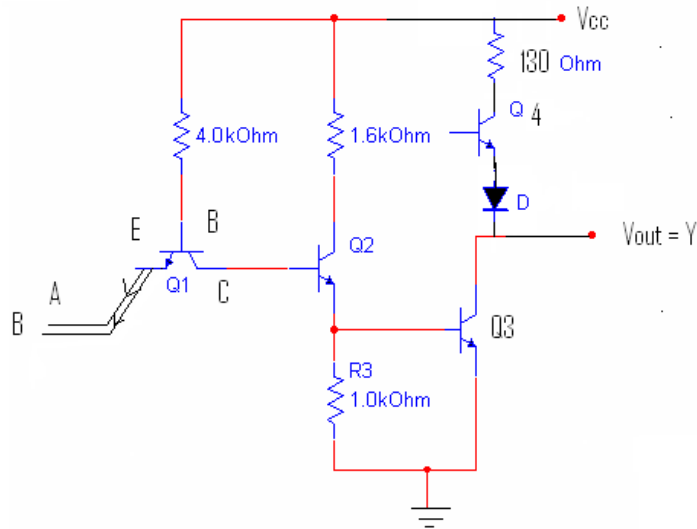


## Totempole output TTL & Schottky TTL

### Totempole output TTL:

If any input is low the collector base junction of  $Q_1$  is reverse biased. At the base of transistor  $Q_1$  has 0.9 V which is not sufficient voltage to drive the transistor  $Q_2$  &  $Q_3$  (i. e, 2.1 V)



**Figure 6.10**

Now  $Q_2$  &  $Q_3$  is in cut off region. When  $Q_2$  is in cut off, the transistor  $Q_4$  is in saturation region, then the output Y becomes high. When all the inputs are high, collector base junction  $Q_1$  is FB, hence the Base of  $Q_1$  has enough voltage to drive the transistor  $Q_2$  &  $Q_3$

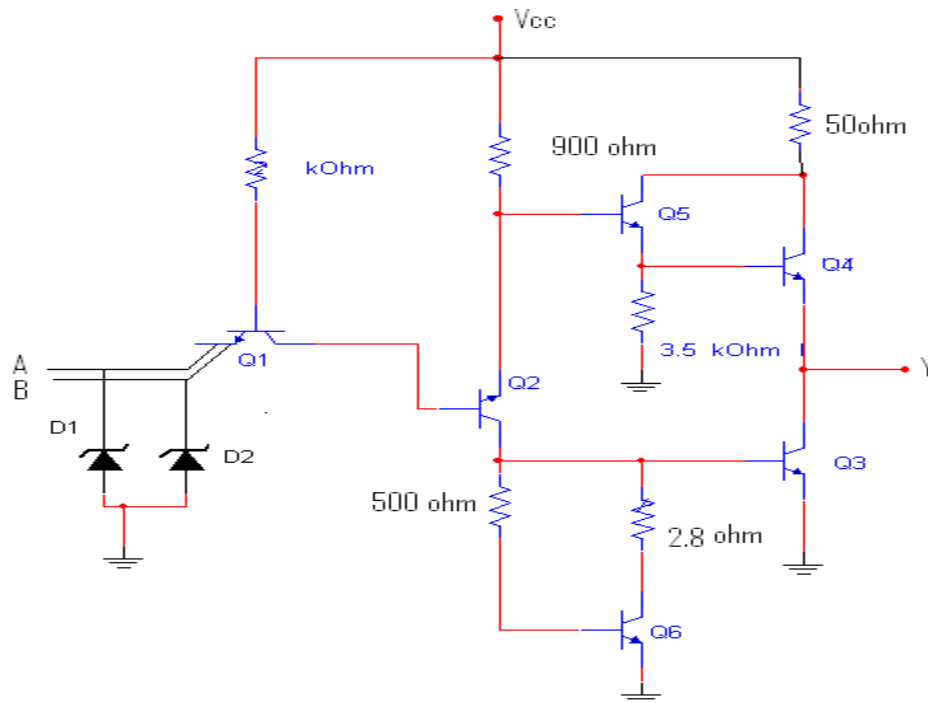
When the transistor  $Q_2$  is in saturation then the transistor  $Q_4$  is entered into the cut off state the output y becomes low.

The need of or the reason for placing the diode in the circuit to provide diode drop in the output path. Thus ensures that  $Q_4$  is cut off when  $Q_3$  is in saturation.

In the case of open collector transistor, the propagation delay is around 35 n sec

During the turn on –off conditions or transients the  $Q_4$  is entered into saturated state. Now the total resistance is  $130\Omega$  saturated resistance of transistor  $Q_4$  + diode internal resistance which is very very low when compared to the pull up resistance in the open collector TTL.

In this way the propagation delay is reduced in totem-pole TTL NAND gate. Disadvantage is power dissipation is more the totem-pole output TTL'S cannot allow the wired logic functions. In the output totem-pole output TTL gates are connected together if one of the output is low and another output is high. The excursive current can produce enough heat to damage the transistors.

**Schottky TTL:****Figure 6.11**

By placing the schottky diode in between each collector and base each saturated transistor. We can further reduce the propagation delay without sacrificing power. The schottky diode can prevent the transistor from going into saturation.

Schottky diode junction is made with one method and one semi conductor material. It differs with the normal diode. In conventional diode, the diode drop is 0.7 V. But by using schottky diodes the diode drop is only 0.4V.

The new combination of Q<sub>4</sub> & Q<sub>5</sub> shall give 2 V<sub>BE</sub> drops, that is necessary to preventing Q<sub>4</sub> from conducting when output is low. The diode D<sub>1</sub> & D<sub>2</sub> and the TTL prevents the negative spikes of the voltage on the input's from damaging the transistor Q<sub>1</sub>. The transistor Q<sub>6</sub> and the two emitter resistance are used to reduce the turn off current spike.